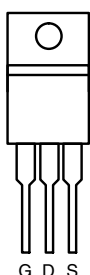


P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 60	0.0195 at $V_{GS} = - 10$ V	- 53	76 nC
	0.0250 at $V_{GS} = - 4.5$ V	- 42	

TO-220AB


Top View

DRAIN connected to TAB

Ordering Information: SUP53P06-20-E3 (Lead (Pb)-free)
SUP53P06-20-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

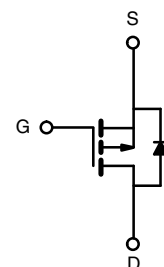
- TrenchFET® Power MOSFET
- 100 % UIS Tested
- Material categorization:
For definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	$T_C = 25$ °C	- 53 ^a	A
	$T_C = 70$ °C	- 46.8	
	$T_A = 25$ °C	9.2 ^b	
	$T_A = 70$ °C	- 8.1 ^b	
Pulsed Drain Current	I_{DM}	- 150	
Avalanche Current Pulse	I_{AS}	- 45	
Single Pulse Avalanche Energy	E_{AS}	101	mJ
Continuous Source-Drain Diode Current	$T_C = 25$ °C	69 ^a	A
	$T_A = 25$ °C	2.1 ^b	
Maximum Power Dissipation	$T_C = 25$ °C	104.2 ^a	W
	$T_C = 70$ °C	66.7 ^a	
	$T_A = 25$ °C	3.1 ^b	
	$T_A = 70$ °C	2 ^b	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	33	40	°C/W
Maximum Junction-to-Case	R_{thJC}	0.98	1.2	

Notes:

a. Based on $T_C = 25$ °C.

b. Surface mounted on 1" x 1" FR4 board.

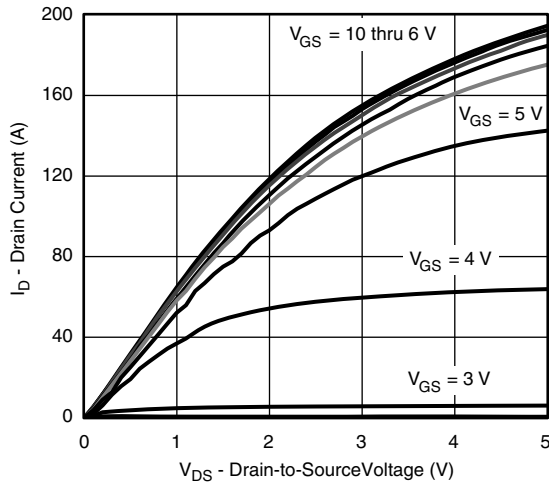
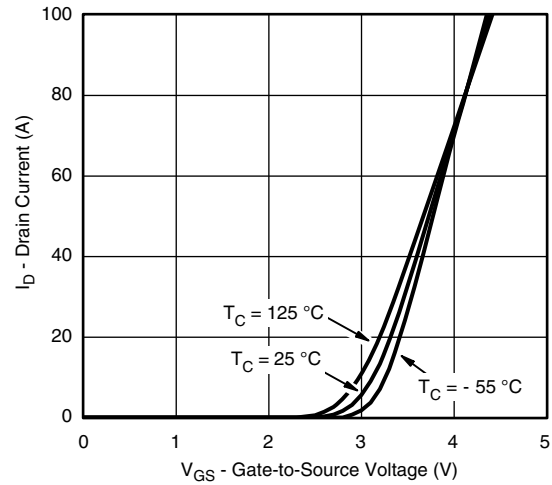
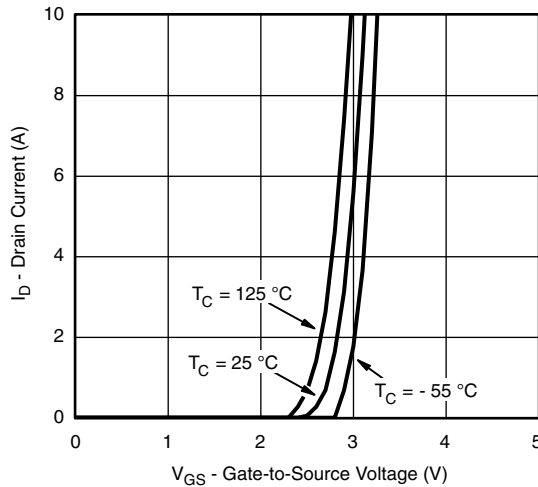
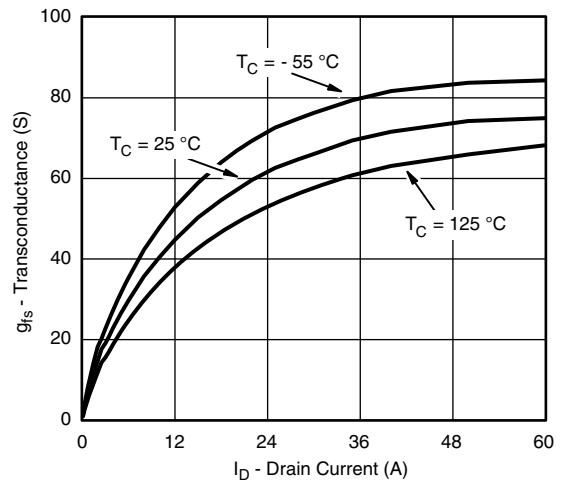
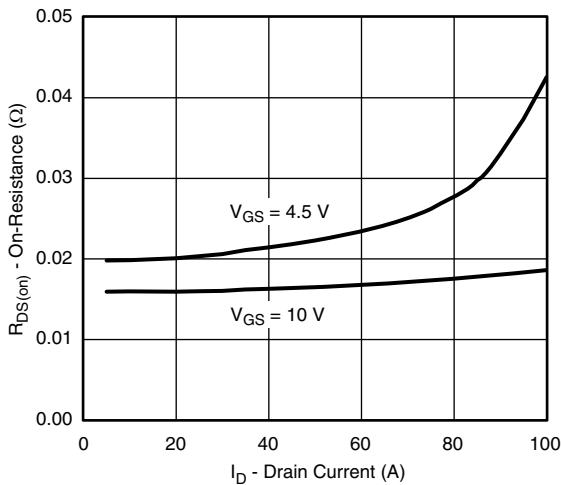
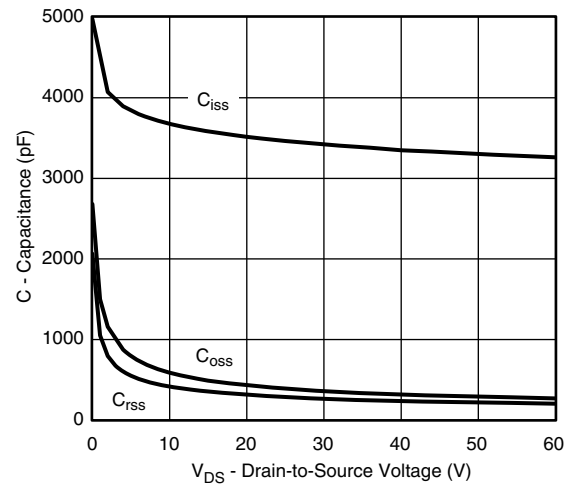
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		68		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.2		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 120			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 30 A		0.0160	0.0195	Ω
		V _{GS} = - 4.5 V, I _D = - 20 A		0.0200	0.0250	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 50 A	20			S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 25 V, V _{GS} = 0 V, f = 1 MHz		3500		pF
Output Capacitance	C _{oss}			390		
Reverse Transfer Capacitance	C _{rss}			290		
Total Gate Charge	Q _g	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 55 A		76	115	nC
		V _{DS} = - 30 V, V _{GS} = - 4.5 V, I _D = - 55 A		38	60	
Gate-Source Charge	Q _{gs}			16		
Gate-Drain Charge	Q _{gd}			19		
Gate Resistance	R _g	f = 1 MHz		5.2		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 2 V, R _L = 2 Ω I _D ≅ - 10 A, V _{GEN} = - 10 V, R _g = 1 Ω		10	15	ns
Rise Time	t _r			7	15	
Turn-Off Delay Time	t _{d(off)}			70	110	
Fall Time	t _f			40	60	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 69	A
Pulse Diode Forward Current ^a	I _{SM}				- 150	
Body Diode Voltage	V _{SD}	I _S = - 30 A		- 1	- 1.5	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 50 A, di/dt = 100 A/μs, T _J = 25 °C		45	68	ns
Body Diode Reverse Recovery Charge	Q _{rr}			59	120	nC
Reverse Recovery Fall Time	t _a			29		ns
Reverse Recovery Rise Time	t _b			16		

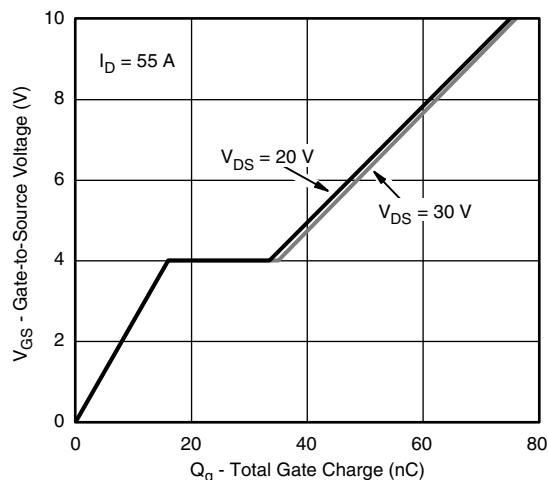
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

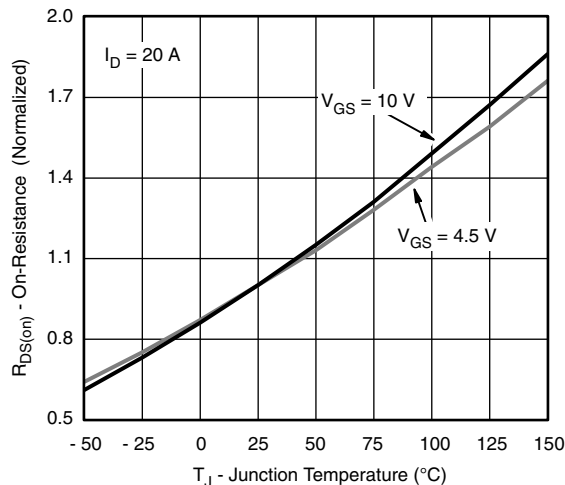
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

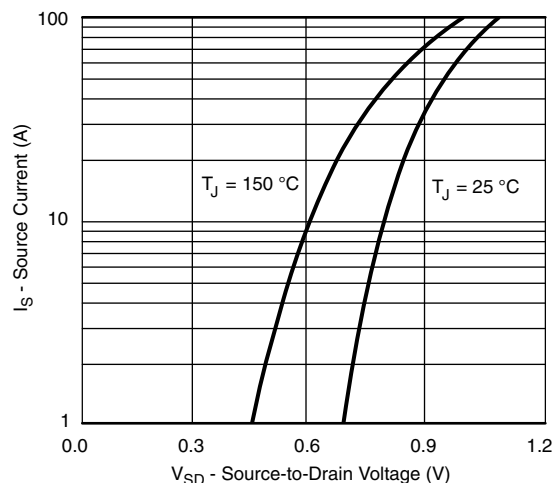
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

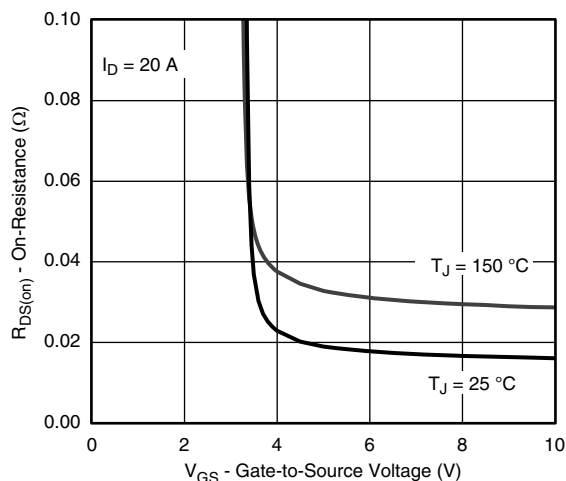
Gate Charge



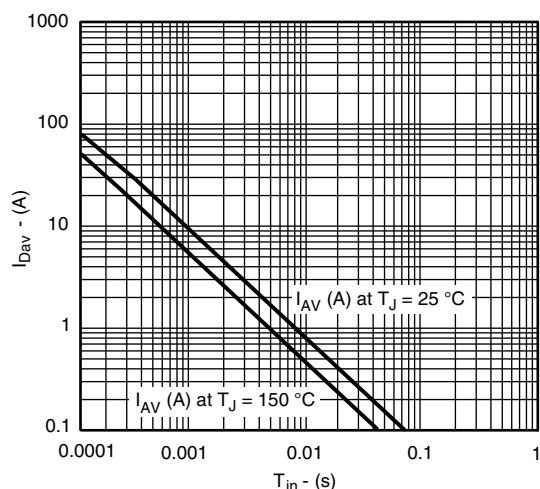
On-Resistance vs. Gate-to-Source Voltage



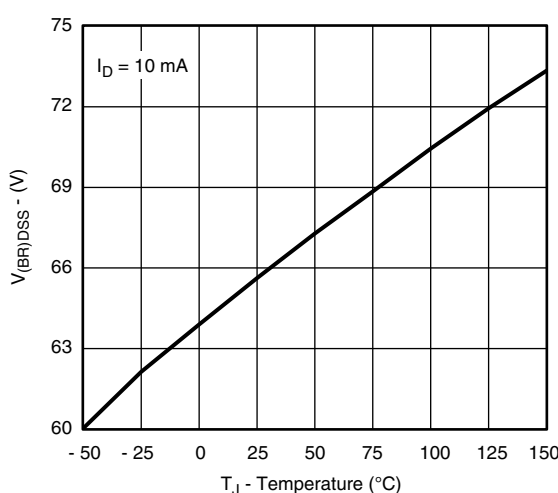
Source-Drain Diode Forward Voltage



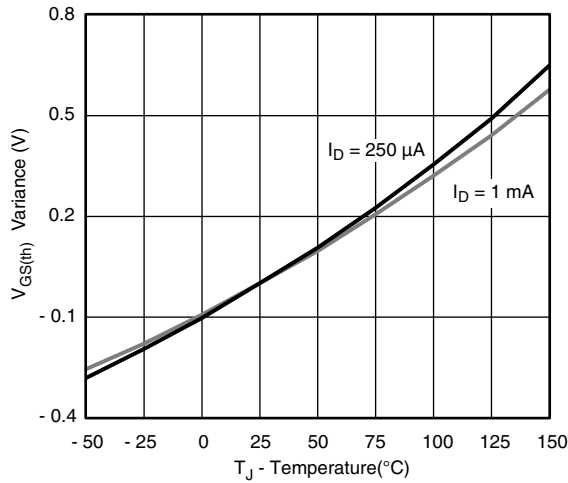
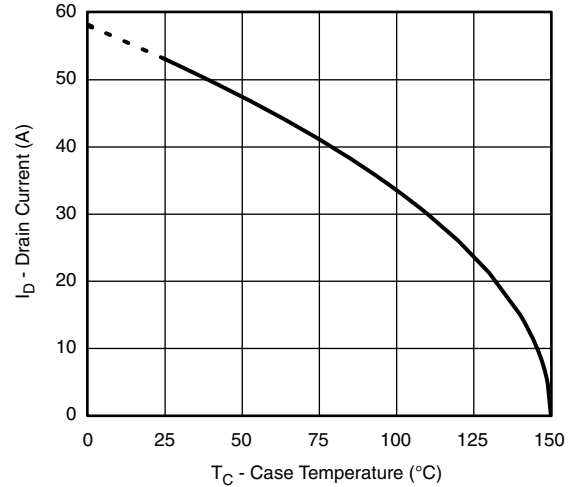
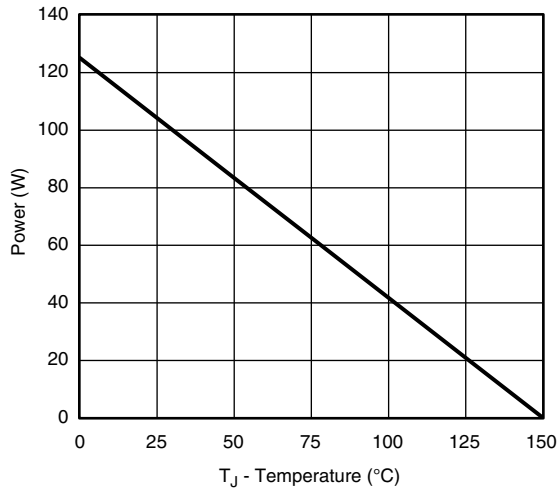
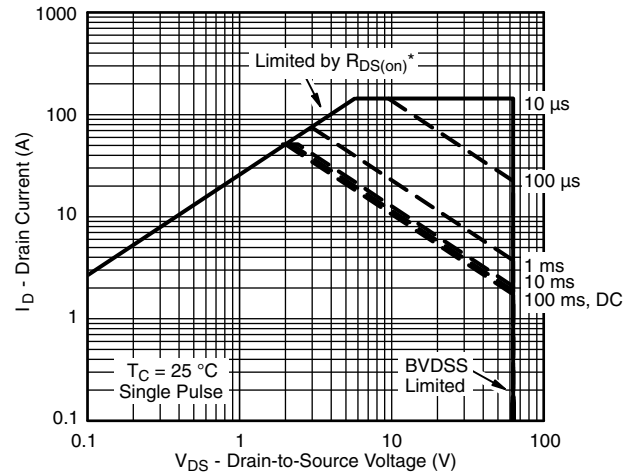
On-Resistance vs. Gate-to-Source Voltage



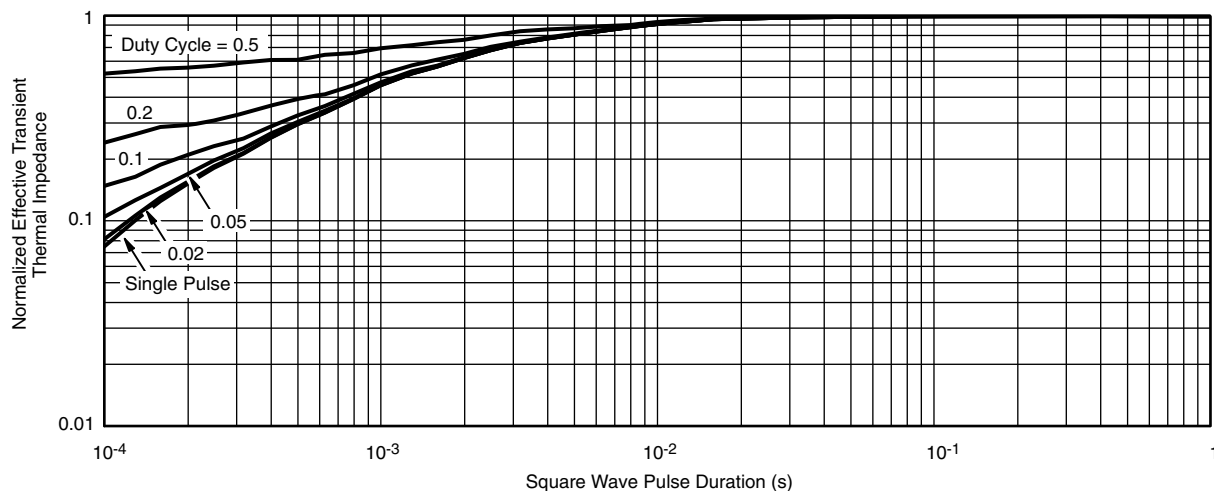
Single Pulse Avalanche Current Capability vs. Time



Drain-Source Breakdown Voltage vs. Junction Temperature

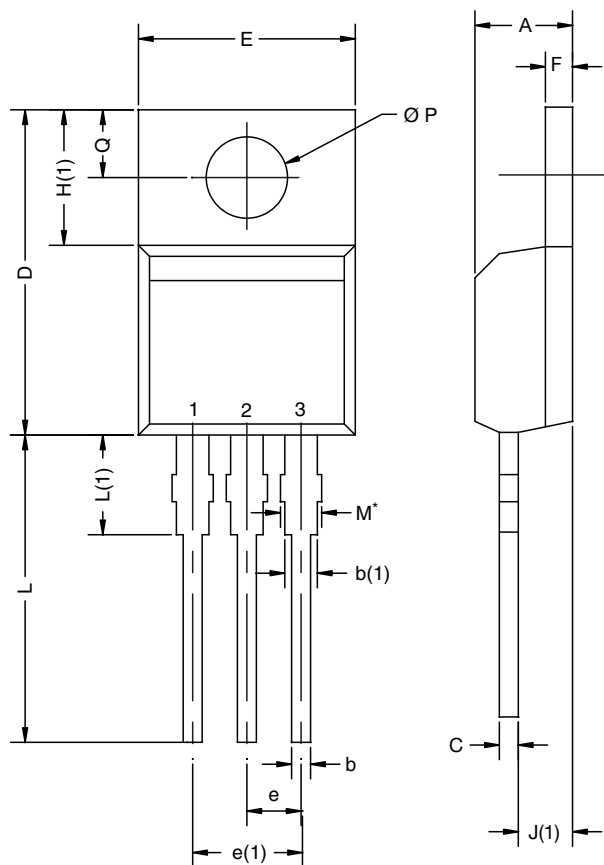
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Threshold Voltage

Max. Drain Current vs. Case Temperature

Power Derating, Junction-to-Case


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

Normalized Thermal Transient Impedance, Junction-to-Case

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TO-220AB

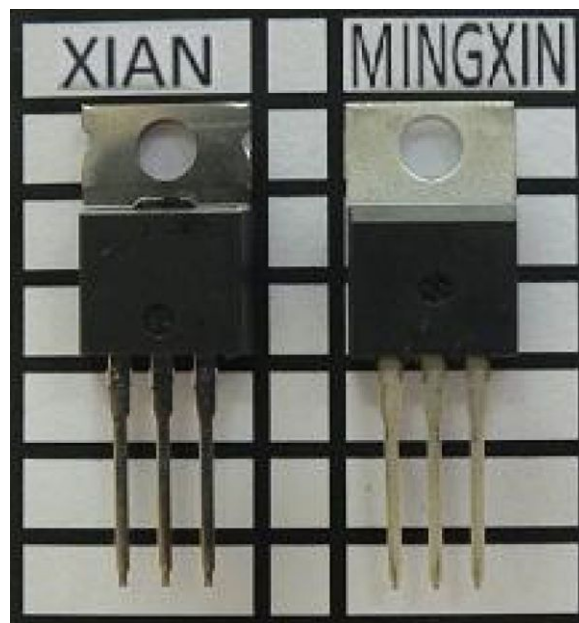


DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
$\varnothing P$	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

- * M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM
- Xi'an and Mingxin actual photo





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